

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Original) A semiconductor device comprising a laminate structure in which an organic insulating film is formed in close contact with a hydrophobic surface of an inorganic insulating film including silicon and nitrogen.
2. (Original) A semiconductor device, comprising:
an inorganic insulating film having a hydrophobic surface and including silicon and nitrogen on a semiconductor layer; and
an organic insulating film formed in close contact with a hydrophobic surface of the inorganic insulating film.
3. (Original) A semiconductor device, comprising:
a first inorganic insulating film on a semiconductor layer;
a second inorganic insulating film having a hydrophobic surface and including silicon and nitrogen on the first inorganic insulating film; and
an organic insulating film formed in close contact with a hydrophobic surface of the second inorganic insulating film.
4. (Original) A semiconductor device according to Claim 3, wherein hydrogen concentration in the second inorganic insulating film is higher than hydrogen concentration in the first inorganic insulating film.
5. (Original) A semiconductor device according to Claim 1, wherein the hydrophobic surface has a contact angle of water of equal to or more than 30°.

6. (Original) A semiconductor device according to Claim 2, wherein the hydrophobic surface has a contact angle of water of equal to or more than 30°.

7. (Original) A semiconductor device according to Claim 3, wherein the hydrophobic surface has a contact angle of water of equal to or more than 30°.

8. (Original) A semiconductor device according to Claim 1, wherein the hydrophobic surface has a contact angle of water of equal to or more than 40°.

9. (Original) A semiconductor device according to Claim 2, wherein the hydrophobic surface has a contact angle of water of equal to or more than 40°.

10. (Original) A semiconductor device according to Claim 3, wherein the hydrophobic surface has a contact angle of water of equal to or more than 40°.

11. (Original) A semiconductor device according to Claim 1, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

12. (Original) A semiconductor device according to Claim 2, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

13. (Original) A semiconductor device according to Claim 3, wherein the inorganic insulating film or the second inorganic insulating film includes oxygen and the nitrogen of equal to or more than 25 atom%.

14. (Original) A semiconductor device according to Claim 1, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

15. (Original) A semiconductor device according to Claim 2, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

16. (Original) A semiconductor device according to Claim 3, wherein the inorganic insulating film or the second inorganic insulating film is a silicon nitride film or a silicon nitride oxide film.

17. (Original) A semiconductor device according to Claim 1, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, for example.

18. (Original) A semiconductor device according to Claim 2, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, for example.

19. (Original) A semiconductor device according to Claim 3, wherein the organic insulating film includes one of or a plurality of organic resin materials selected from acrylic resin, polyamide, or polyimide of photosensitive or nonphotosensitive, for example.

20. – 35. (Cancelled)